

SEMICONDUCTOR TECHNICAL DATA

KDS2236M/S

VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR DIODE

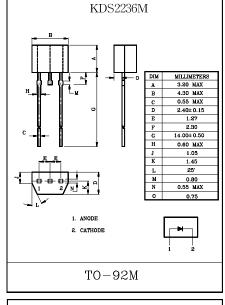
AFC APPLICATION FOR FM RECEIVER.

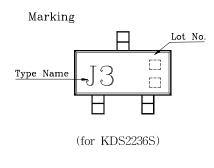
FEATURES

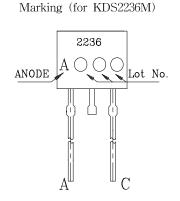
 $\begin{array}{ll} \bullet \mbox{ High Q} & : \mbox{ Q=70(Min.) (f=50MHz)}. \\ \bullet \mbox{ Low Reverse Current} : \mbox{ I}_R=100nA(Max.) (\mbox{ } V_R=4V). \end{array}$

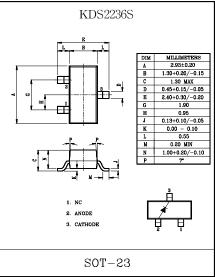
MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_{R}	15	V
Junction Temperature	$T_{\rm j}$	150	$^{\circ}$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}$ C









ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	${ m I}_{ m R}$	V_R =4 V	-	-	100	nA
Total Capacitance	C_{T}	V _R =4V, f=1MHz	7.0	-	14	pF
Capacitance Ratio	K	(Note)	0.210	-	0.5	
Figure of Merit	Q	V_R =4V, f=50MHz	70	120	-	

Note) K=
$$\frac{C_T(@V_R=2V, f=1MHz)-C_T(@V_R=4V, f=1MHz)}{C_T(@V_R=4V, f=1MHz)}$$

